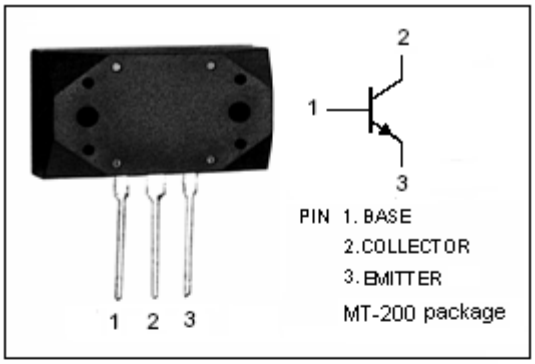
isc Silicon NPN Power Transistor 2SD1037



DESCRIPTION

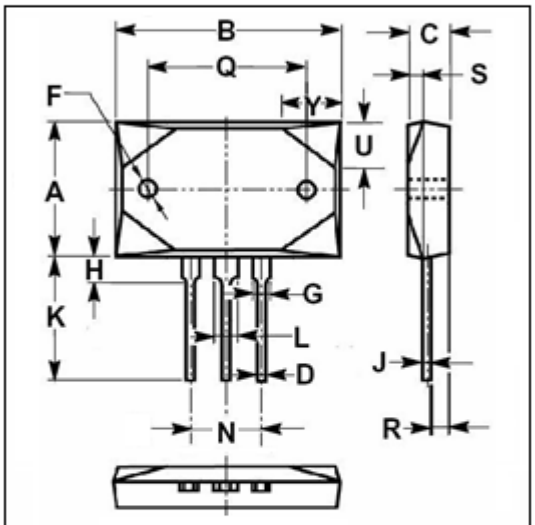
- High Collector-Emitter Breakdown Voltage-
  $V_{(BR)CEO}$= 150V(Min)
- Good Linearity of h_{FE}

APPLICATIONS

- Designed for audio and general purpose applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	150	V
V_{CEO}	Collector-Emitter Voltage	120	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	30	A
P_C	Collector Power Dissipation @ T_C=25℃	180	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	21.30	21.70
B	36.10	36.70
C	5.80	6.20
D	1.04	1.07
F	3.10	3.30
G	1.90	2.10
H	3.80	4.00
J	0.55	0.85
K	20.00	20.30
L	2.90	3.10
N	10.70	11.10
Q	24.00	24.40
R	2.90	3.30
S	2.00	2.20
U	6.90	7.10
Y	8.90	9.10

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 50mA ; I_B= 0	120			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 10A; I_B= 1A			0.5	V
$V_{bE(sat)}$	Base-Emitter Saturation Voltage	I_C= 10A; I_B= 1A			1.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 80V; I_E= 0			5	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 6V; I_C=0			5	μA
h_{FE}	DC Current Gain	I_C= 10A; V_{CE}= 4V	20			
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 10V;f_{test}= 1.0MHz		210		pF
f_T	Current-Gain—Bandwidth Product	I_E= -2A; V_{CE}= 12V		1.5		MHz